



**ZXMN10A11K**

**100V N-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
100V	350mΩ @ $V_{GS} = 10V$	3.5A
	450mΩ @ $V_{GS} = 6V$	3.1A

**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

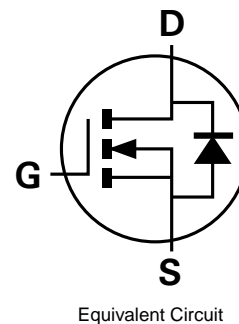
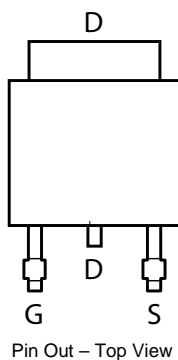
- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

**Features and Benefits**

- Fast switching speed
- Low input capacitance
- “Green” Component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

**Mechanical Data**

- Case: TO252-3L
- Case Material: Molded Plastic “Green” Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

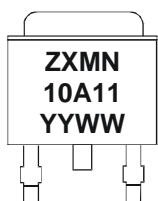


**Ordering Information** (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN10A11KTC	See Below	13	16	2,500

Note: 1. Diodes, Inc. defines “Green” products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.’s “Green” Policy can be found on our website. For packaging details, go to our website.

**Marking Information**



ZXMN = Product Type Marking Code, Line 1  
 10A11 = Product Type Marking Code, Line 2  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01-52)

**Maximum Ratings** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

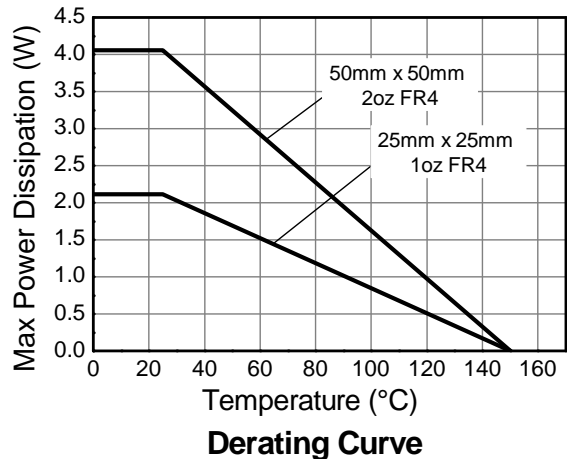
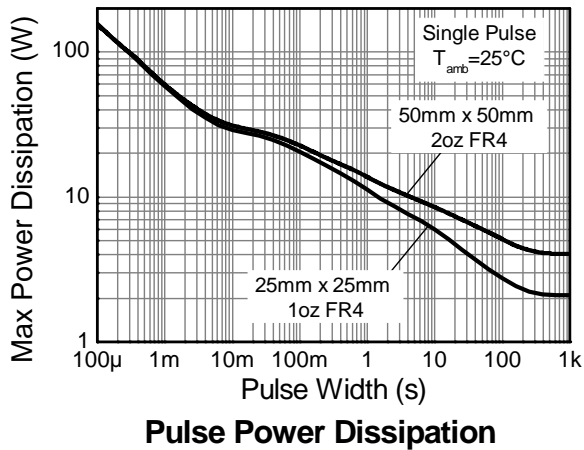
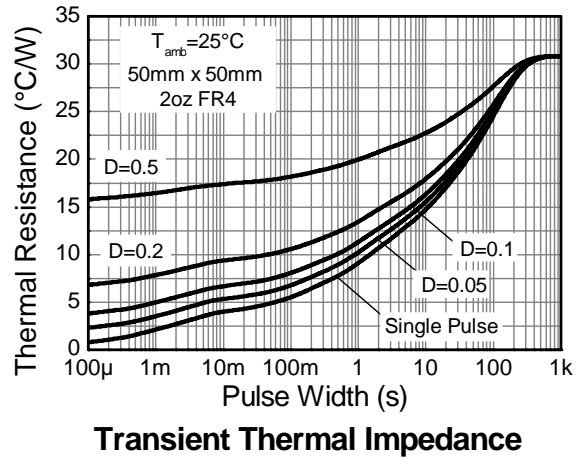
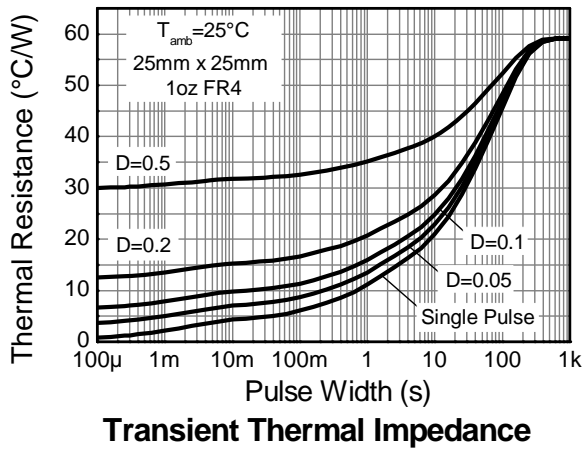
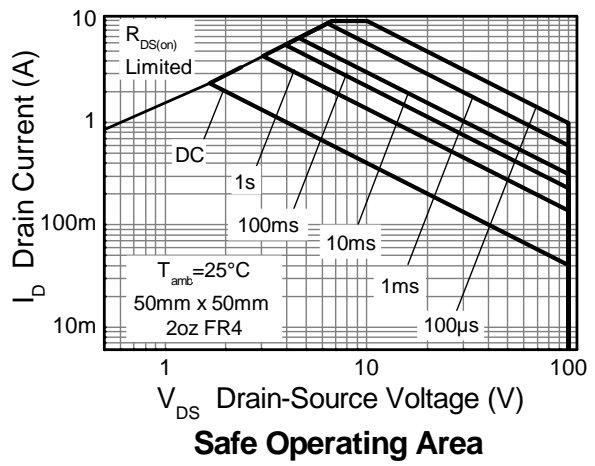
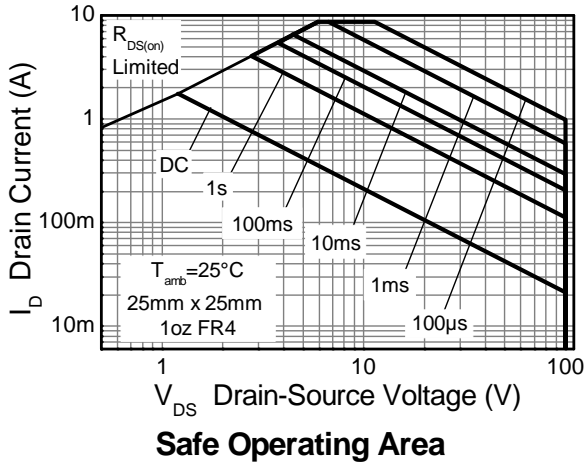
Characteristic			Symbol	Value	Unit	
Drain-Source voltage			$V_{DSS}$	100	V	
Gate-Source voltage			$V_{GS}$	$\pm 20$	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 3)	$I_D$	3.5	A	
		$T_A = 70^\circ\text{C}$ (Note 3)		2.8		
		(Note 2)		2.4		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 4)	$I_{DM}$	9.9	A	
Continuous Source current (Body diode)			(Note 3)	$I_S$	8.4	A
Pulsed Source current (Body diode)			(Note 4)	$I_{SM}$	9.9	A

**Thermal Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	$P_D$	4.06	W mW/ $^\circ\text{C}$
			32.4	
	(Note 3)		8.5	
	(Note 6)		68.0	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	2.11	$^\circ\text{C/W}$
	(Note 3)		16.8	
	(Note 6)		30.8	
Thermal Resistance, Junction to Lead	(Note 2)	$R_{\theta JL}$	14.7	$^\circ\text{C/W}$
	(Note 3)		59.1	
	(Note 6)		1.10	
Operating and storage temperature range		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

- Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  3. Same as note 2, except the device is measured at  $t \leq 10$  sec.
  4. Same as note 2, except the device is pulsed with  $D = 0.02$  and pulse width 300  $\mu\text{s}$ . The pulse current is limited by the maximum junction temperature.
  5. Thermal resistance from junction to solder-point (at the end of the drain lead).
  6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with the high coverage single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

**Thermal Characteristics**

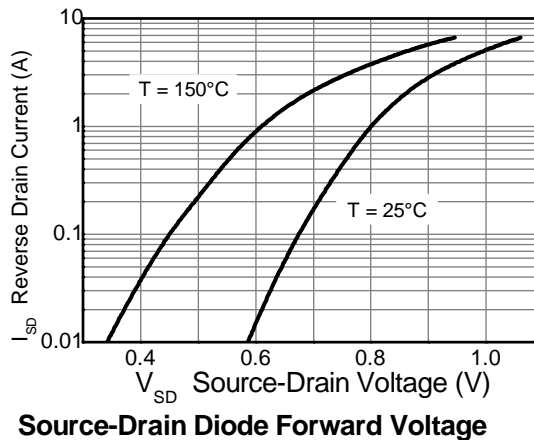
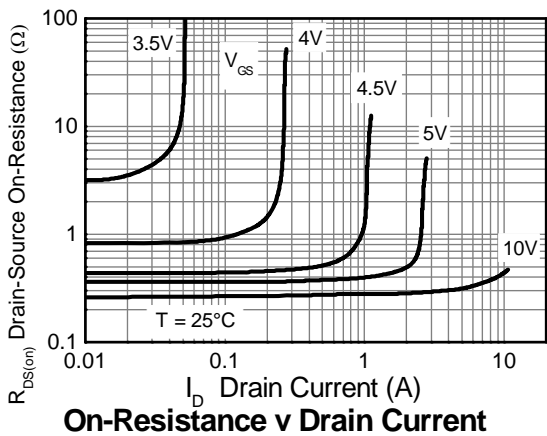
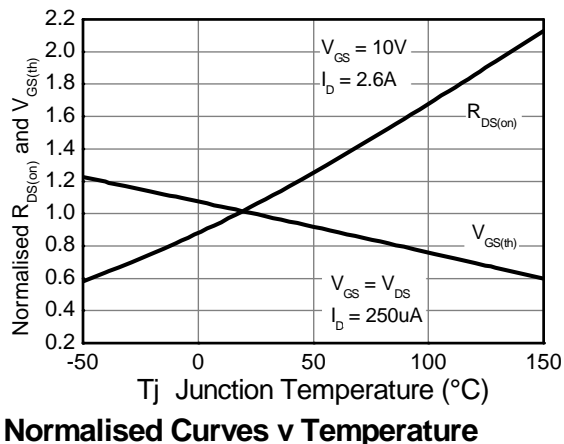
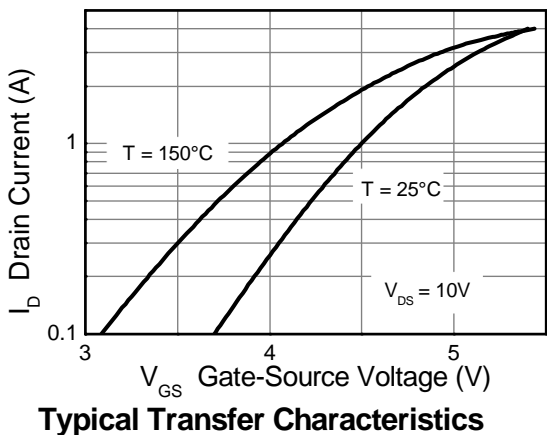
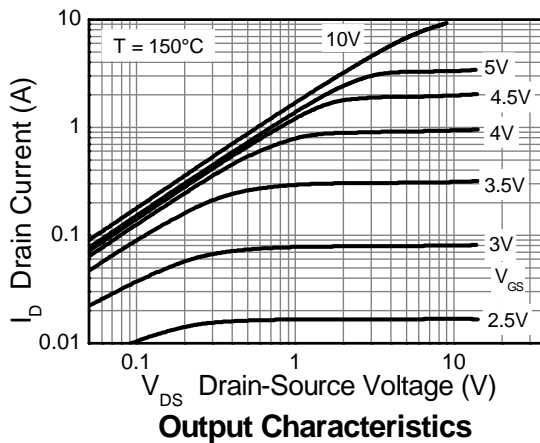
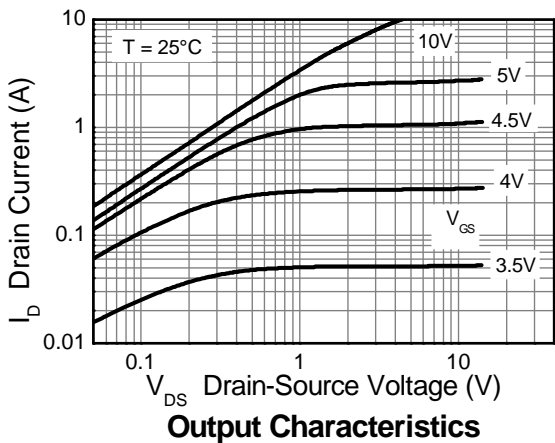


**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

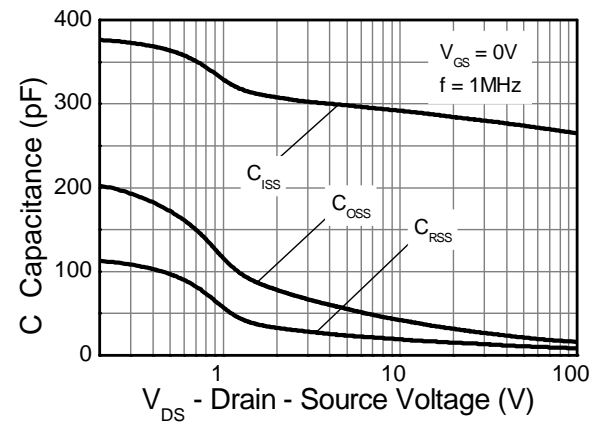
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	2	—	4	V	I <sub>D</sub> = 250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(on)</sub>	—	—	0.350	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.6A
				0.450		V <sub>GS</sub> = 6V, I <sub>D</sub> = 1.3A
Forward Transconductance (Notes 7 & 8)	g <sub>fs</sub>	—	4	—	S	V <sub>DS</sub> = 15V, I <sub>D</sub> = 2.6A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	—	0.850	0.950	V	I <sub>S</sub> = 1.85A, V <sub>GS</sub> = 0V
Reverse recovery time (Note 8)	t <sub>rr</sub>	—	26	—	ns	I <sub>S</sub> = 1.0A, di/dt = 100A/μs
Reverse recovery charge (Note 8)	Q <sub>rr</sub>	—	30	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	274	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	21	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	11	—	pF	
Total Gate Charge (Note 9)	Q <sub>g</sub>	—	3.5	—	nC	V <sub>GS</sub> = 6V
Total Gate Charge (Note 9)	Q <sub>g</sub>	—	5.4	—	nC	V <sub>GS</sub> = 10V
Gate-Source Charge (Note 9)	Q <sub>gs</sub>	—	1.4	—	nC	
Gate-Drain Charge (Note 9)	Q <sub>gd</sub>	—	1.5	—	nC	
Turn-On Delay Time (Note 9)	t <sub>D(on)</sub>	—	2.7	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V I <sub>D</sub> = 1.0A, R <sub>G</sub> ≅ 6Ω
Turn-On Rise Time (Note 9)	t <sub>r</sub>	—	1.7	—	ns	
Turn-Off Delay Time (Note 9)	t <sub>D(off)</sub>	—	7.4	—	ns	
Turn-Off Fall Time (Note 9)	t <sub>f</sub>	—	3.5	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
  8. For design aid only, not subject to production testing.
  9. Switching characteristics are independent of operating junction temperatures.

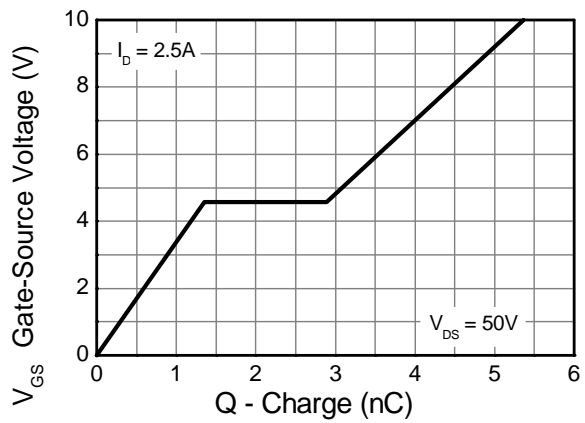
Typical Characteristics



Typical Characteristics - continued

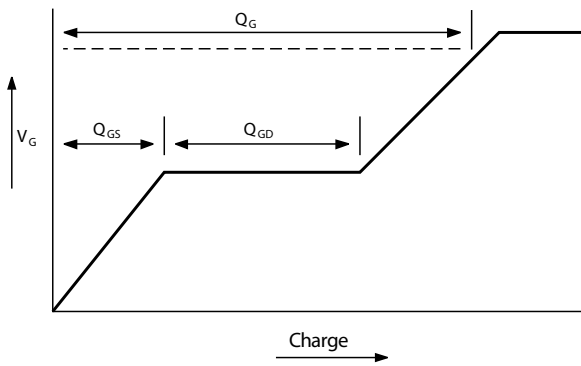


Capacitance v Drain-Source Voltage

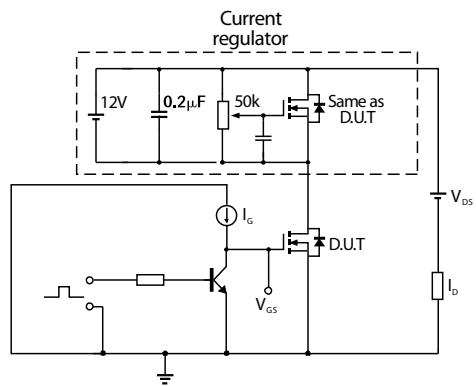


Gate-Source Voltage v Gate Charge

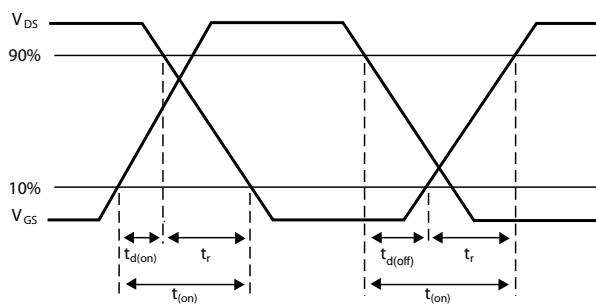
Test Circuits



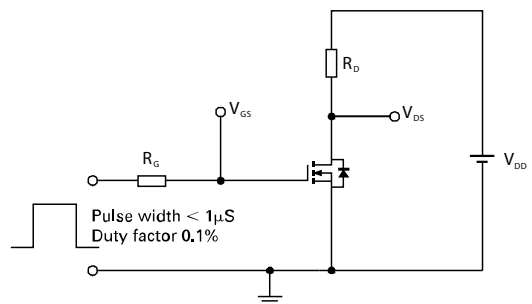
Basic gate charge waveform



Gate charge test circuit

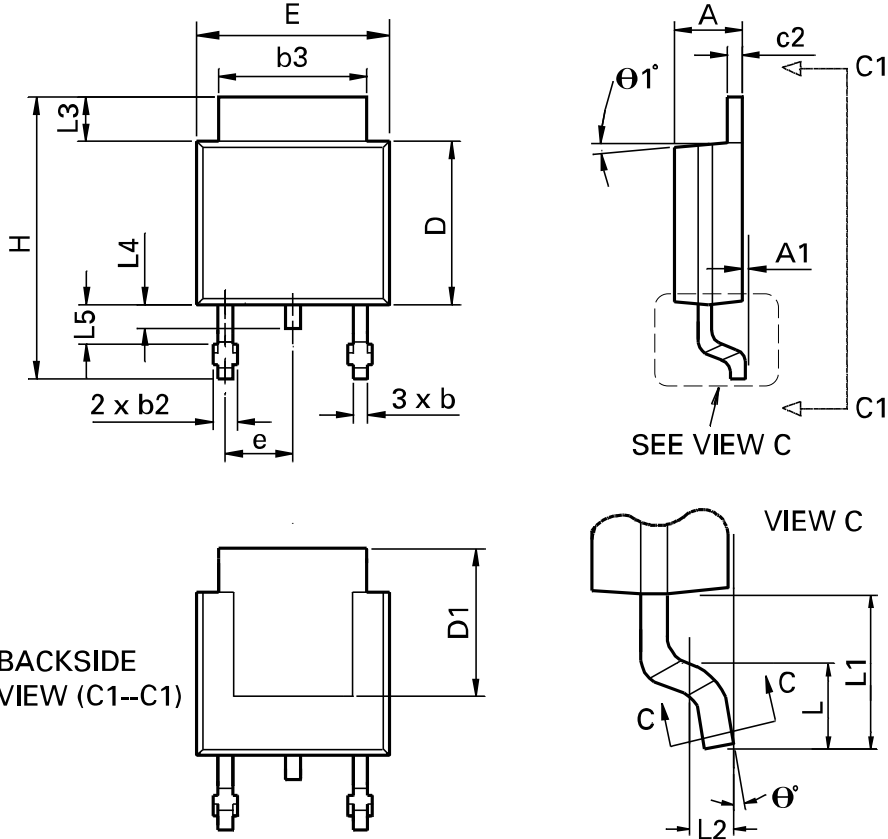


Switching time waveforms



Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	$\theta1^\circ$	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	$\theta^\circ$	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-